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PSMN025-100D

N-channel TrenchMOS SiliconMAX standard level FET

Rev. 4 — 12 January 2012

Product data sheet

1. Product profile

1.1 General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

■ DC-to-DC converters

Switched-mode power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u> ; see <u>Figure 4</u>	-	-	47	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	150	W
Static chara	acteristics					
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	22	25	mΩ
Dynamic cl	haracteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 45 \text{ A}; V_{DS} = 80 \text{ V};$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure } 13}{\text{ Composition}}$	-	25	-	nC



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		<u>-</u>
2	D	drain[1]	mb	D
3	S	source		
mb	D	mounting base; connected to drain	1 3	mbb076 S
			SOT428 (DPAK)	

^[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN025-100D	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V_{DGR}	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{see } \frac{\text{Figure 1}}{\text{Model}}$	-	33	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{see } \frac{\text{Figure 4}}{\text{Figure 4}}};$	-	47	Α
I _{DM}	peak drain current	pulsed; T _{mb} = 25 °C; see Figure 4	-	188	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	150	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-dra	ain diode				
Is	source current	T _{mb} = 25 °C	-	47	Α
I _{SM}	peak source current	pulsed; T _{mb} = 25 °C	-	188	Α
Avalanche	ruggedness				
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 40 A; V_{sup} ≤ 25 V; unclamped; t_p = 100 μs ; R_{GS} = 50 Ω	-	260	mJ
I _{AS}	non-repetitive avalanche current	$V_{sup} \le 25 \text{ V}$; $V_{GS} = 10 \text{ V}$; $T_{j(init)} = 25 \text{ °C}$; $R_{GS} = 50 \Omega$; unclamped; see Figure 3	-	47	Α

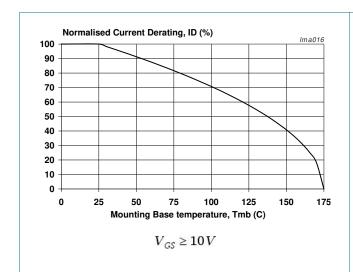


Fig 1. Continuous drain current as a function of mounting base temperature

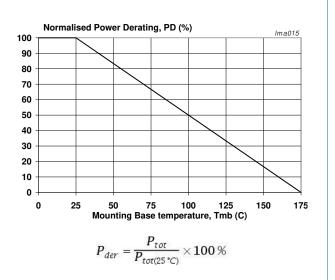


Fig 2. Normalized total power dissipation as a function of mounting base temperature

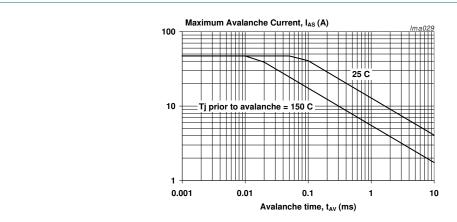


Fig 3. Maximum permissible non-repetitive avalanche current as a function of avalanche time

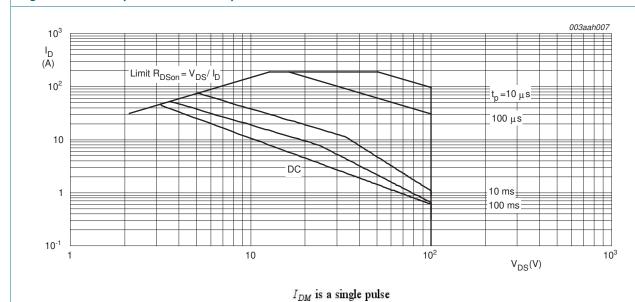


Fig 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	-	1	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	SOT428 package ; printed-circuit board mounted ; minimum footprint	-	50	-	K/W

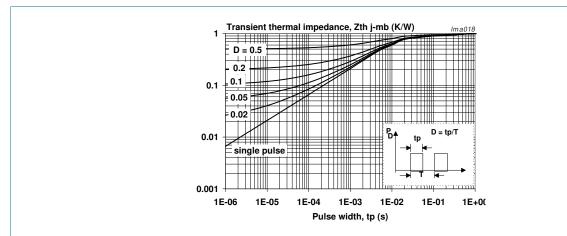


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS} drain-source break voltage	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	89	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
$V_{GS(th)}$ gate-source thr	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see Figure 9	1		V	
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	2 3 4	4	V	
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 9	-	-	6	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 °C;$ see Figure 11	-	-	68	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 11; see Figure 12	-	22	25	mΩ
Dynamic o	characteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 45 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$	-	61	-	nC
Q_{GS}	gate-source charge	$T_j = 25 ^{\circ}\text{C}$; see <u>Figure 13</u>	-	13	-	nC
Q_{GD}	gate-drain charge		-	25	-	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2600	-	рF
C _{oss}	output capacitance	$T_j = 25 ^{\circ}C$; see <u>Figure 14</u>	-	340	-	pF
C_{rss}	reverse transfer capacitance		-	195	-	рF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 1.8 \Omega; V_{GS} = 10 \text{ V};$	-	18	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \Omega; T_j = 25 ^{\circ}C$	-	72	-	ns
$t_{d(off)}$	turn-off delay time		-	69	-	ns
t _f	fall time		-	58	-	ns
L _D	internal drain inductance	measured from tab to centre of die ; $T_j = 25 ^{\circ}\text{C}$	-	3.5	-	nΗ
L _S	internal source inductance	measured from source lead to source bond pad; $T_j = 25$ °C	-	7.5	-	nΗ
Source-dr	rain diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 15	-	0.87	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	82	-	ns
Qr	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; T_j = 25 \text{ °C}$	-	0.26	-	μC

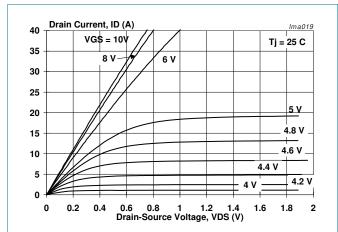


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical function of drain-source voltage; typical values

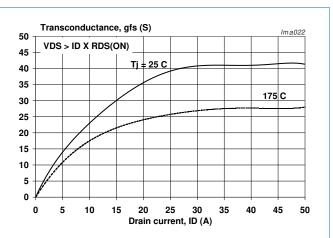


Fig 7. Forward transconductance as a function of drain current; typical values

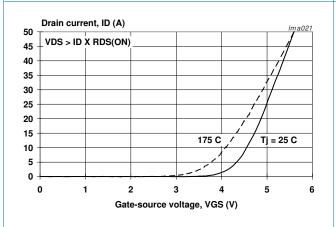
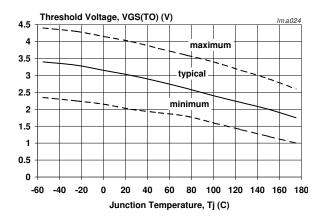


Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$I_D = 1mA; V_{DS} = V_{GS}$$

Fig 9. Gate-source threshold voltage as a function of junction temperature

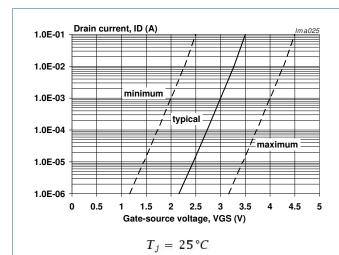
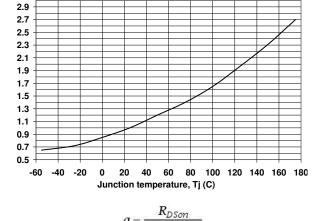


Fig 10. Sub-threshold drain current as a function of gate-source voltage



 $a-R_{DSon(25\,^{\circ}C)}$

Fig 11. Normalized drain source on-state resistance factor as a function of junction temperature

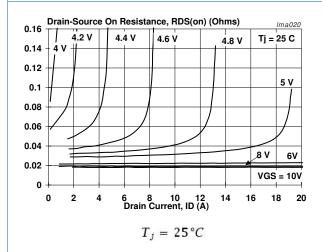


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

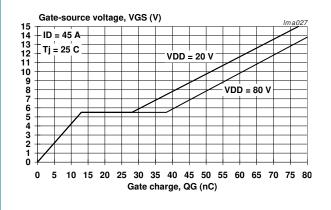


Fig 13. Gate-source voltage as a function of gate charge; typical values

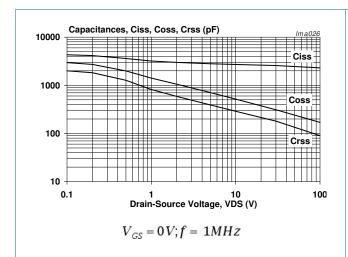


Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

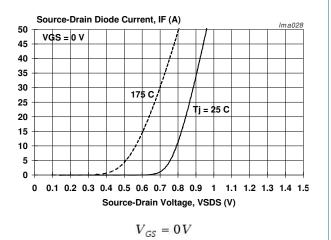


Fig 15. Source current as a function of source-drain voltage; typical values

7. Package outline

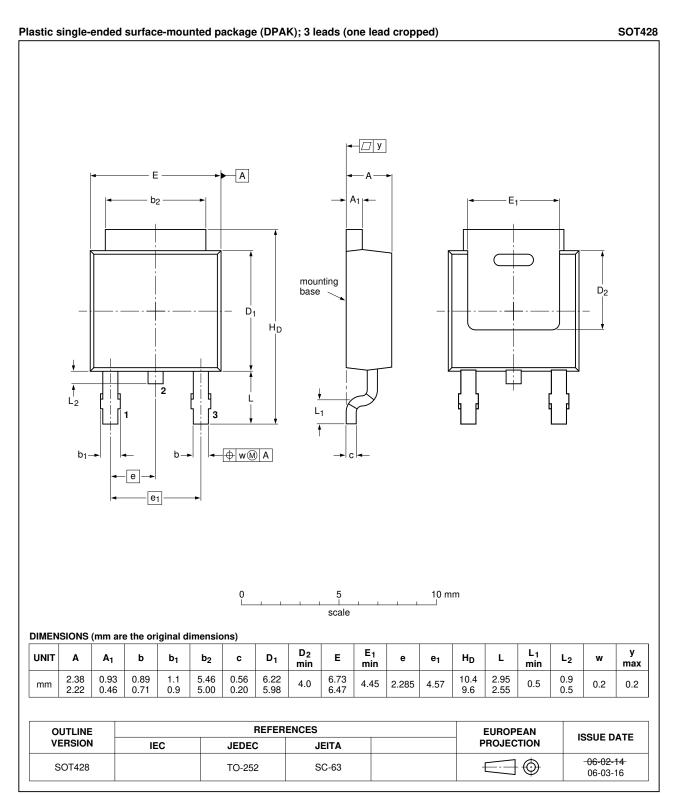


Fig 16. Package outline SOT428 (DPAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN025-100D v.4	20120112	Product data sheet	-	PSMN025-100D v.3
Modifications:	 Various change 	es to content.		
PSMN025-100D v.3	20081120	Product data sheet	-	PSMN025-100D v.2

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PSMN025-100D

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N-channel TrenchMOS SiliconMAX standard level FET

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